

**Claims**

- 1 1. A method for performing proximity effect correction on a layout of an integrated  
2 circuit defined by a computer readable layout file, to produce a corrected layout file, the  
3 method comprising:  
4 receiving a polygon from the computer readable layout file, the polygon  
5 corresponding to a portion of the integrated circuit;  
6 performing using a data processor a fragmentation of the polygon into a set of  
7 smaller shapes, based upon parameters of a manufacturing tool used for implementing the  
8 layout;  
9 performing using a data processor a proximity effect correction of at least one of  
10 the smaller shapes in the set of smaller shapes to provide a computer readable corrected  
11 layout file comprising a modified set of smaller shapes;  
12 and  
13 providing the computer readable corrected layout file to said manufacturing tool.
- 1 2. The method of claim 1, wherein the manufacturing tool comprises a mask writer.
- 1 3. The method of claim 1, wherein the manufacturing tool comprises a vector scan,  
2 e-beam tool, and said parameters comprise scanning dimensions of said vector scan, e-  
3 beam tool.
- 1 4. The method of claim 1, wherein one of said parameters is a minimum dimension  
2 for the manufacturing tool, and the fragmentation is such that the smaller shapes do not  
3 have a dimension smaller than said minimum dimension after said correction.
- 1 5. The method of claim 1, wherein one of said parameters is a maximum dimension  
2 for the manufacturing tool, and the fragmentation is such that the smaller shapes do not  
3 have a dimension larger than said maximum dimension after said correction.

- 1 6. The method of claim 1, wherein the corrected layout file is used to make a binary  
2 mask.
- 1 7. The method of claim 1, wherein the corrected layout file is used to make an  
2 attenuated phase-shifting mask.
- 1 8. The method of claim 1, wherein the corrected layout file is used to make a tri-tone  
2 phase-shifting mask.
- 1 9. The method of claim 1, wherein the corrected layout file is used to make an  
2 alternating aperture phase-shifting mask.
- 1 10. The method of claim 9, wherein two edges of one of the shapes in the set of  
2 smaller shapes are adjacent to two distinct phase-shifting regions, the two phase-shifting  
3 regions are substantially out of phase, and including storing information indicating that  
4 said two edges of one of the shapes in the set of smaller shapes are adjacent to two  
5 distinct phase-shifting regions.
- 1 11. The method of claim 10, wherein said information about the two edges is used to  
2 facilitate the phase assignment of the phase-shifting regions.
- 1 12. The method of claim 1, wherein at least one edge of one shape abuts a boundary  
2 of a critical area of the layout.
- 1 13. The method of claim 1, wherein the manufacturing tool comprises a mask  
2 inspection tool.
- 1 14. The method of claim 1, wherein a boundary between adjacent shapes in the set of  
2 smaller shapes is adjusted to account for a position of an edge of at least one of the  
3 adjacent shapes which is modified by the proximity effect correction.

1 15. The method of claim 1, wherein a second polygon within proximity range of the  
2 polygon is taken into account in the fragmentation of the shapes.

1 16. The method of claim 15, wherein a corner of the second polygon is used in the  
2 fragmentation of the shapes.

1 17. A mask for defining a layer of material, said mask comprising:  
2 a mask substrate;  
3 a layout data file used to create a layout pattern on the mask substrate;  
4 said layout pattern comprising material or physical shapes for transfer of an image  
5 to a workpiece;  
6 and said layout pattern having at least one shape having at least one segment  
7 corrected for proximity effects, said such shape was defined before correction by  
8 fragmenting a polygon of the layout data file, based upon parameters of a manufacturing  
9 tool used for implementing the layout.

1 18. A method for manufacturing integrated circuits, said integrated circuits being  
2 defined by a computer readable layout file, the method comprising:  
3 receiving a polygon from the computer readable layout file, the polygon  
4 corresponding to a portion of the integrated circuit;  
5 performing using a data processor a fragmentation of the polygon into a set of  
6 smaller shapes, based upon parameters of a manufacturing tool used for implementing the  
7 layout;  
8 performing using a data processor a proximity effect correction of at least one of  
9 the smaller shapes in the set of smaller shapes to provide a computer readable corrected  
10 layout file comprising a modified set of smaller shapes;  
11 and  
12 providing the computer readable corrected layout file to said manufacturing tool.  
13 producing a mask having a mask layout based on the corrected layout file;  
14 and  
15 exposing a semiconductor treated with a material sensitive to radiation energy to  
16 said radiation energy using said mask.

1 19. The method of claim 18, where the mask is produced using a vector-scan e-beam  
2 tool by exposing a mask blank coated with an e-beam sensitive resist and said resist  
3 polarity is chosen such that the shapes representing the critical dimensions of the layout  
4 are exposed on the mask.

1 20. A method for producing a mask for a layer on an integrated circuit represented by  
2 a computer readable layout file, comprising:  
3 receiving a polygon from the computer readable layout file, the polygon  
4 corresponding to a portion of the integrated circuit;  
5 performing using a data processor a fragmentation of the polygon into a set of  
6 smaller shapes, based upon parameters of a manufacturing tool used for implementing the  
7 layout;  
8 performing using a data processor a proximity effect correction of at least one of  
9 the smaller shapes in the set of smaller shapes to provide a computer readable corrected  
10 layout file comprising a modified set of smaller shapes;  
11 and  
12 producing a mask having a mask layout based on the corrected layout file.

1 21. A system for producing layout data, comprising:  
2 a data processor which executes programs of instruction;  
3 memory accessible by the data processor and storing programs of instruction, the  
4 programs of instruction including logic to receive a polygon of a computer readable  
5 layout file of a portion of the integrated circuit, performing using a data processor a  
6 fragmentation of the polygon into a set of smaller shapes, based upon parameters of a  
7 manufacturing tool used for implementing the layout, performing using a data processor a  
8 proximity effect correction of at least one of the smaller shapes in the set of smaller  
9 shapes to provide a computer readable corrected layout file comprising a modified set of  
10 smaller shapes.

1    22.    An article of manufacture, comprising a machine readable data storage medium  
 2    storing programs of instruction, including logic to receive a polygon of a computer  
 3    readable layout file of a portion of the integrated circuit, performing using a data  
 4    processor a fragmentation of the polygon into a set of smaller shapes, based upon  
 5    parameters of a manufacturing tool used for implementing the layout, performing using a  
 6    data processor a proximity effect correction of at least one of the smaller shapes in the set  
 7    of smaller shapes to provide a computer readable corrected layout file comprising a  
 8    modified set of smaller shapes.

1    23.    A method for performing proximity effect correction on a layout of an integrated  
 2    circuit defined by a computer readable layout file, to produce a corrected layout file, the  
 3    method comprising:  
 4        receiving a polygon from the computer readable layout file, the polygon  
 5        corresponding to a portion of the integrated circuit;  
 6        performing using a data processor a fragmentation of at least one edge of the  
 7        polygon into a set of segments, based upon parameters of a manufacturing tool used for  
 8        implementing the layout;  
 9        performing using a data processor a proximity effect correction of at least  
 10       one of the segments in the set of segments to provide a computer readable corrected  
 11       layout file;  
 12       and  
 13       providing the computer readable corrected layout file to said manufacturing  
 14       tool.

1    24.    A method for manufacturing integrated circuits, said integrated circuits being  
 2    defined by a layout file, the method comprising:  
 3        receiving a polygon from the computer readable layout file, the polygon  
 4        corresponding to a portion of the integrated circuit;  
 5        performing using a data processor a fragmentation of at least one edge of the  
 6        polygon into a set of segments, based upon parameters of a manufacturing tool used for  
 7        implementing the layout;

8 performing using a data processor a proximity effect correction of at least  
9 one of the segments in the set of segments to provide a computer readable corrected  
10 layout file;  
11 producing a mask having a mask layout based on the corrected layout file;  
12 and  
13 exposing a semiconductor treated with a material sensitive to radiation energy to  
14 said radiation energy using said mask.

1 25. The method of claim 24, where the mask is produced using a vector-scan e-beam  
2 tool by exposing a mask blank coated with an e-beam sensitive resist and said resist  
3 polarity is chosen such that the shapes representing the critical dimensions of the layout  
4 are exposed on the mask.